

G 1
Concl'd.

patent no. 5,976,940. Moreover, this patent claims priority to Japanese Application No. P07-322962, filed December 12, 1995, which application is incorporated by reference to the extent permitted by law.--.

5 On page 21, line 12, replace "first embedded diffusion layer 131 has" with --first embedded diffusion layer 131 may include a peak position 600 of an impurity concentration that may reside at a first distance from a datum surface of the substrate 111 (for example an arbitrary surface used as a
10 reference, such as a bottom surface of the substrate 111).
The first embedded diffusion layer 131 has--.

G 2
On page 22, line 2, replace "high." with --high.
Additionally, the second embedded diffusion layer 151 may include a peak position 700 of an impurity concentration that 15 may reside at a second distance from the datum surface of the substrate 111 such that the first distance (peak position 600 of Figure 6 to the datum surface of the substrate 111) may be greater than the second distance (peak position 700 of Figure 7 to the datum surface of the substrate 111).--

20 IN THE CLAIMS
Please amend claims 1, 3, 4, 6, 17, 19 and 20 and add new claims 21-23 as follows:

G 3
1 1. (Amended Five Times) A semiconductor device,
2 comprising:
3 [a first vertical type bipolar transistor and a second
4 vertical type bipolar transistor whose voltage is different
5 from that of said first vertical type bipolar transistor
6 formed on a semiconductor substrate made by forming]
7 a substrate defining a datum surface;